Ordering number : ENA0094

SANYO Semiconductors
DATA SHEET

N-Channel Silicon MOSFET

CPH3442 — General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		30	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		6.5	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	26	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm²×0.8mm)	1.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	0.4		1.4	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=3A	6	10		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=3A, V_{GS}=4V		17	24	mΩ
	R_{DS}(on)2	I_D=1.5A, V_{GS}=2.5V		22	31	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		1295		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		239		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		183		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		21		ns
Rise Time	t_r	See specified Test Circuit.		85		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit.		156		ns
Fall Time	t_f	See specified Test Circuit.		125		ns

Marking : ZR

Continued on next page.

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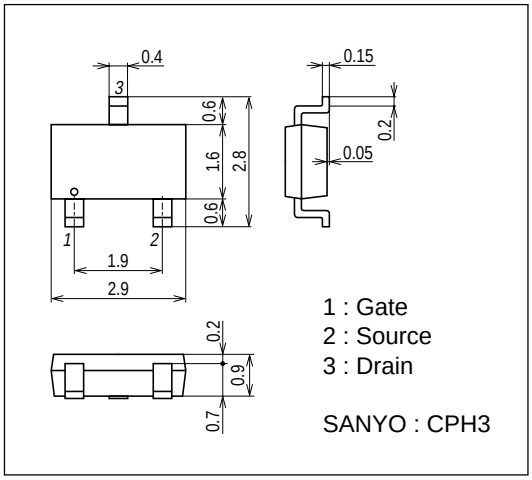
Continued from preceding page.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=4V, I_D=6.5A		16.1		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=4V, I_D=6.5A		2.8		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=10V, V_{GS}=4V, I_D=6.5A		5.7		nC
Diode Forward Voltage	V_{SD}	I_S=6.5A, V_{GS}=0V		0.82	1.2	V

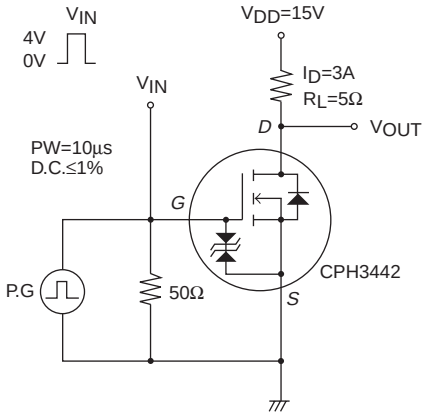
Package Dimensions

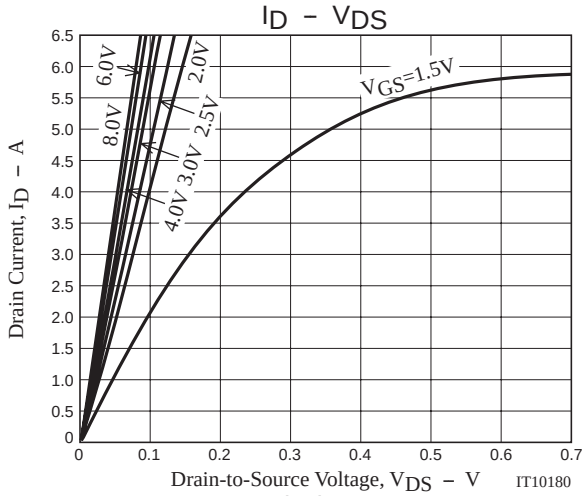
unit : mm

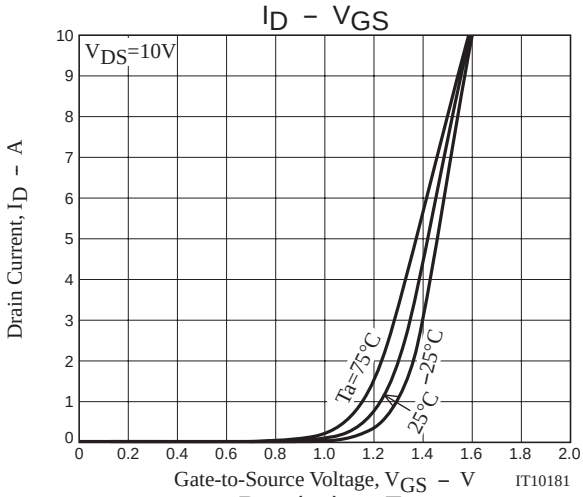
7015-004

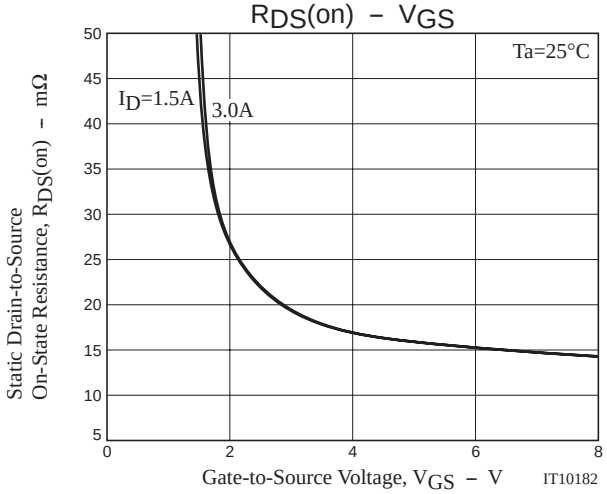


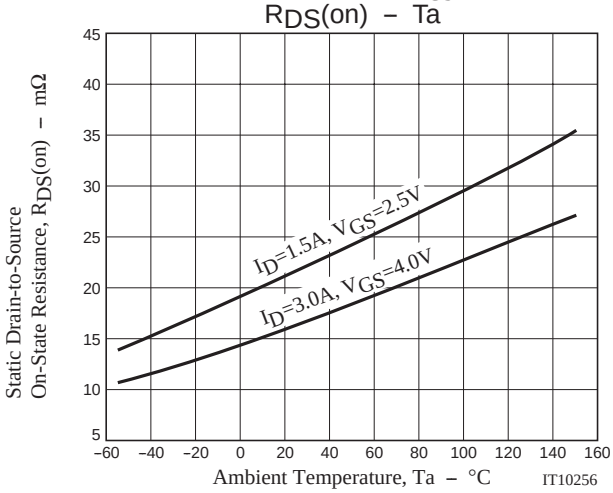
Switching Time Test Circuit

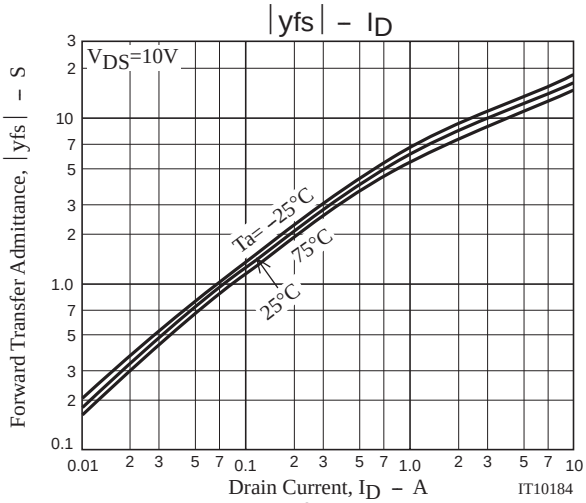


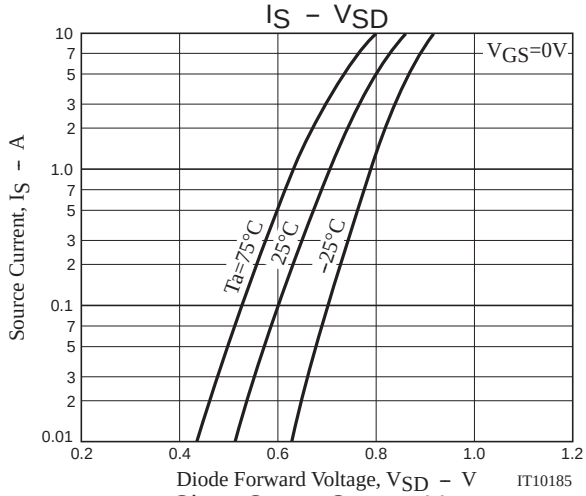


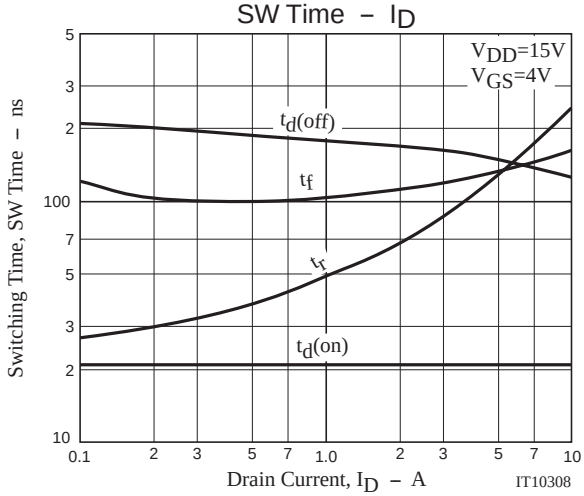


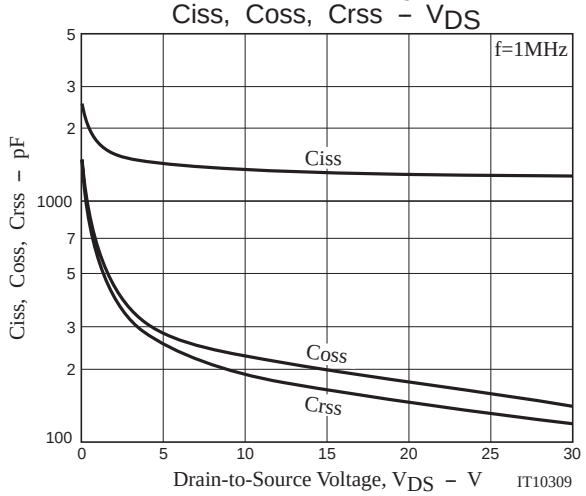


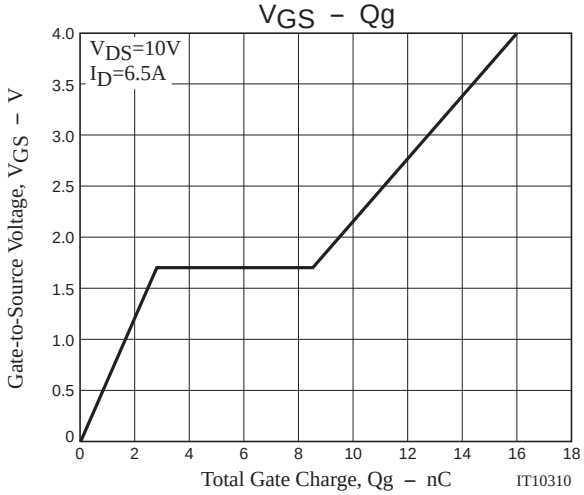


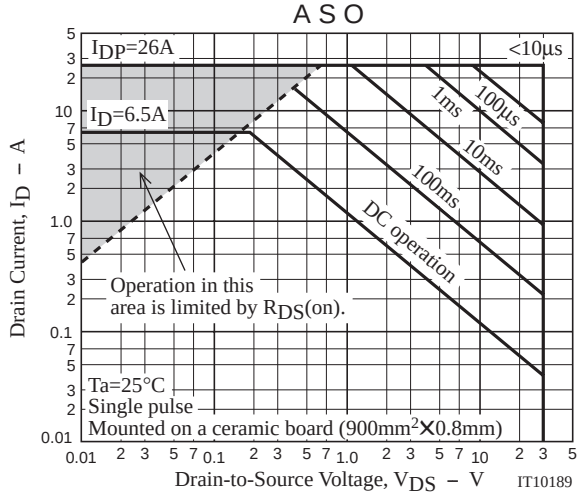

|yfs| – ID
VDS=10V
Ta= –25°C
75°C
25°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT10184

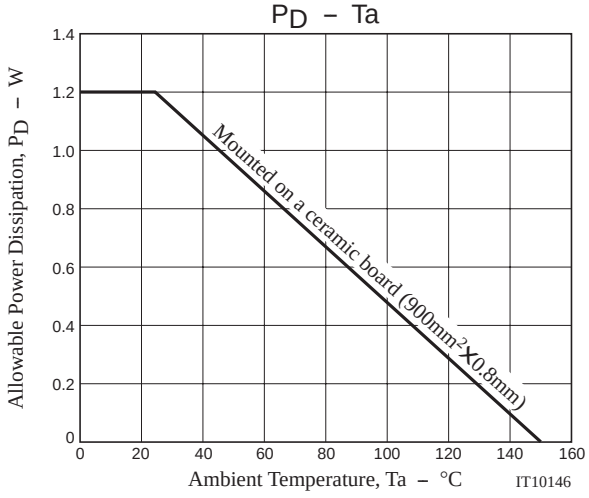

IS – VSD
VGS=0V
Ta=75°C
25°C
–25°C
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT10185


SW Time – ID
VDD=15V
VGS=4V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT10308


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT10309


VGS – Qg
VDS=10V
ID=6.5A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT10310


A S O
IDP=26A
<10µs
ID=6.5A
1ms
100µs
10ms
100ms
DC operation
Operation in this
area is limited by RDS(on).
Ta=25°C
Single pulse
Mounted on a ceramic board (900mm2×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT10189


PD – Ta
Mounted on a ceramic board (900mm2×0.8mm)
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT10146

Note on usage : Since the CPH3442 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.